

## 1. Description

TPD 4E1U06 Is an electrostatic discharge (ESD) protection diode based on a four-channel one-way transient voltage suppressor (TVS), with ultra-low capacitance. The ESD shock dissipation value of this device is higher than the highest level stipulated by the IEC 61000-4 -2 international standard.

## 3. Features

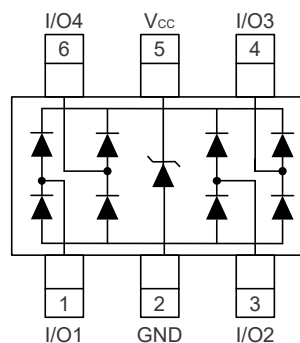
- IEC 61000-4-2 4 ESD protection
  - ± 15kV, with contact discharge
  - ± 15kV, air-gap discharge
- IEC61000-4-4 Transient discharge (EFT) protection
  - 80A (5/50ns )
- IEC61000-4-5 Surge protection
  - 3A (8/20μ s)

## 2. Application

- USB 2.0
- Ethernet
- Differential signaling (LVDS)
- HD Multimedia interface (HDMI) control line  
Mobile
- industry processor interface (MIPI) bus Low Pressure

- IO capacitance: 0.8 pF (typical value)
- DC breakdown voltage: 6.5V (minimum)
- Ultra-low leakage current: 10 nA (max.)
- Low ESD clamp voltage
- easy-to-wire DCK and DBV packages
- Industrial temperature range:-40°C to 125°C  
Small

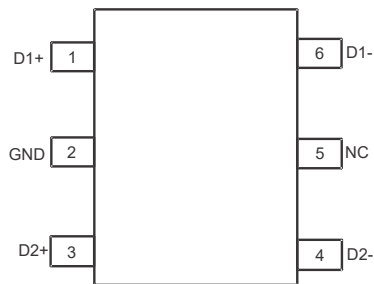
## 4. Pinning information



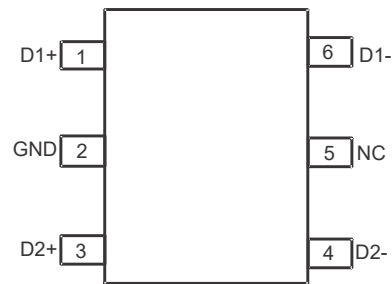
**SOT23-6**



## 5.Pin Configuration and Functions



DCK Package 6-Pin  
SC70-6 Top View



DBV Package 6-Pin  
SOT-23 Top View

PIN		I/O	DESCRIPTION
NAME	NO		
D1+	1	I/O	ESD protected channel. Connect to data line as close to the connector as possible
D1-	6	I/O	
D2-	4	I/O	
D2+	3	I/O	
GND	2	GND	Ground. Connect to ground
NC	5	I/O	No connect. Can be left floating, grounded, or connected to $V_{CC}$



## 6. Absolute Maximum Ratings $T_A = 25^\circ\text{C}$

Parameter	Symbol	MIN	MAX	Units
IEC 61000-4-4 EFT protection (5/50 ns)			80	A
IEC 61000-4-5 surge protection (8/20 $\mu\text{s}$ ) peak pulse current	$I_{PP}$		3	A
IEC 61000-4-5 surge protection (8/20 $\mu\text{s}$ ) peak pulse power	$P_{PP}$		45	W
Junction Temperature		-40	125	$^\circ\text{C}$
Storage temperature	$T_{STG}$	-65	115	$^\circ\text{C}$

## 7. ESD Ratings

		VALUE	Units
$V_{(ESD)}$ Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001, all pins <sup>(1)</sup>	$\pm 4000$	V
	Charged device model (CDM), per JEDEC specification JESD22-C101 all pins <sup>(2)</sup>	$\pm 1500$	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

## 8. ESD Ratings - IEC Specification

		VALUE	Units
$V_{(ESD)}$ Electrostatic discharge	IEC 61000-4-2 contact ESD	$\pm 15000$	V
	IEC 61000-4-2 air-gap ESD	$\pm 15000$	V

## 9. Recommended Operating Conditions

		MIN	MAX	Units
$V_{IO}$	Input pin voltage	0	5.5	V
$T_A$	Operating free-air temperature	-40	125	V

over operating free-air temperature range (unless otherwise noted)



## 10. Thermal Information

THERMAL METRIC <sup>(1)</sup>	Symbol	DBV (SOT-23)	DBV (SOT-23)	Units
		6 PINS	6 PINS	
Junction-to-ambient thermal resistance	$R_{\theta JA}$	224.3	224.3	°C/W
Junction-to-case (top) thermal resistance	$R_{\theta JC(top)}$	166.1	166.1	°C/W
Junction-to-board thermal resistance	$R_{\theta JB}$	68.4	68.4	°C/W
Junction-to-top characterization parameter	$\Psi_{JT}$	57.3	57.3	°C/W
Junction-to-board characterization parameter	$\Psi_{JB}$	67.9	67.9	°C/W



## 11. Electrical Characteristic ( $T_A=25^\circ\text{C}$ unless otherwise noted)

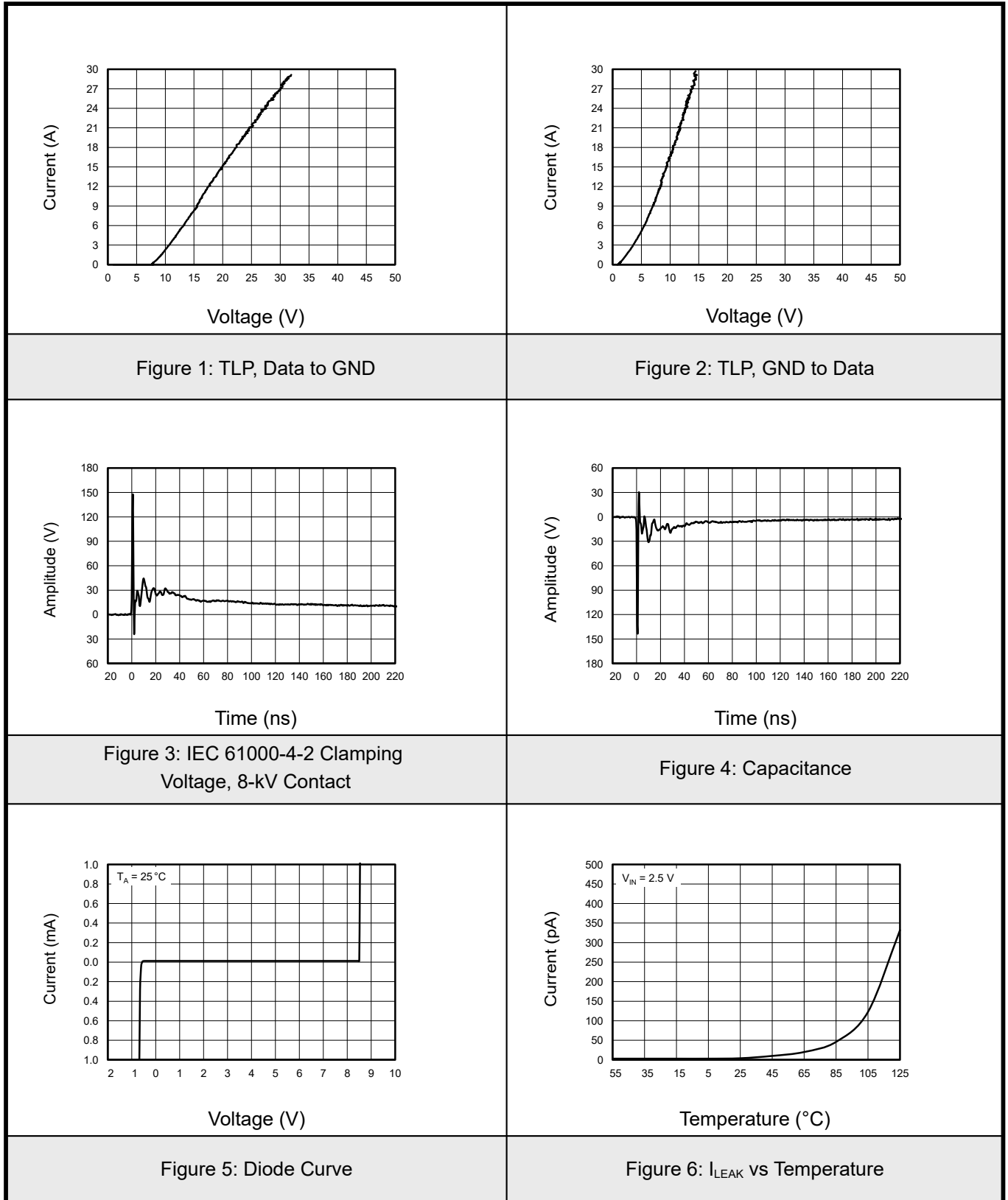
Parameter	Symbol	Conditions	Min	Typ	Max	Units
Reverse stand-off voltage	$V_{RWM}$	$I_{IO}=10\mu\text{A}$			5.5	V
Clamp voltage with ESD strike	$V_{CLAMP}$	$I_{PP}=1\text{A}, t_p=8/20\mu\text{s}, \text{from I/O to GND}^{(1)}$		11		V
		$I_{PP}=3\text{A}, t_p=8/20\mu\text{s}, \text{from I/O to GND}^{(1)}$		15		V
Dynamic resistance	$R_{DYN}$	Pin x to GND pin <sup>(2)</sup>		1		$\Omega$
		GND to pin x		0.6		$\Omega$
Line capacitance	$C_L$	$f=1\text{MHz}, V_{BIAS}=2.5\text{V}, 25^\circ\text{C}$		0.8	1	pF
Channel to channel input capacitance	$C_{CROSS}$	Pin2=0V, $f=1\text{MHz}, V_{BIAS}=2.5\text{V}$		0.006	0.015	pF
		between channel pins		0.01	0.025	pF
Variation of channel input capacitance	$\Delta_{CIO-TO-GND}$	Pin2=0V, $f=1\text{MHz}, V_{BIAS}=2.5\text{V}$ , channel_x pin to ground – channel_y pin to ground		0.025	0.07	pF
Break-down voltage, IO to GND	$V_{BR}$	$I_{IO}=1\text{mA}$	6.5		8.5	V
Leakage current	$I_{LEAK}$	$V_{IO}=2.5\text{V}$		1	10	nA

(1) Non-repetitive current pulse 8/20  $\mu\text{s}$  exponentially decaying waveform according to IEC61000-4-5.

(2) Extraction of RDYN using least squares fit of TLP characteristics between  $I = 10\text{A}$  and  $I = 20\text{A}$ .

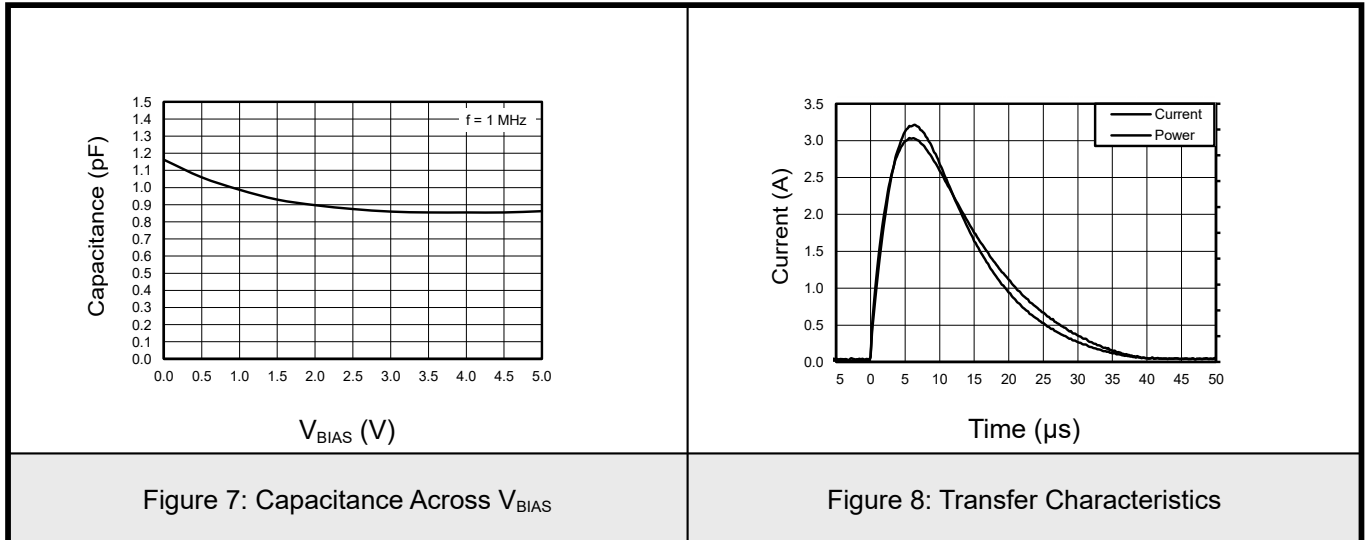


## 12.1 Typical characteristic





## 12.2 Typical characteristic





## 13. Detailed Description

The TPD4E1U06 is a quad channel unidirectional TVS ESD protection diode with ultra low capacitance. This device can dissipate ESD strikes above the maximum level specified by the IEC 61000-4-2 international standard. Typical application areas include HDMI, USB2.0, MHL, and DisplayPort. Its 0.8-pF line capacitance makes it suitable for a wide range of applications.

### Functional Block Diagram

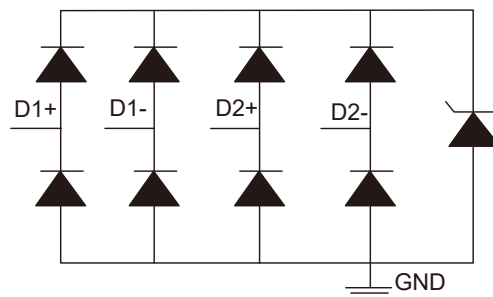


Figure 9. Circuit Schematic Diagram

### Feature Description

#### IEC 61000-4-2 Level 4 ESD Protection

The I/O pins can withstand ESD events up to  $\pm 15$ -kV contact and air. An ESD/surge clamp diverts the current to ground.

#### IEC 61000-4-5 Surge Protection

The IO pins can withstand surge events up to 3 A and 45 W (8/20- $\mu$ s waveform). An ESD-surge clamp diverts this current to ground.

#### IEC 61000-4-4 EFT Protection

The IO pins can withstand an electrical fast transient burst of up to 80 A (5/50-ns waveform, 4 kV with 50- $\Omega$  impedance). An ESD-surge clamp diverts the current to ground.

#### IO Capacitance

The capacitance between each I/O pin to ground is 0.8 pF.

#### DC Breakdown Voltage

The DC breakdown voltage of each I/O pin is a minimum of 6.5 V. This ensures that sensitive equipment is protected from surges above the reverse standoff voltage of 5.5 V.

#### Ultra Low Leakage Current

The I/O pins feature an ultra-low leakage current of 10 nA (Maximum) with a bias of 2.5 V.

#### Low ESD Clamping Voltage

The I/O pins feature an ESD clamp that is capable of clamping the voltage to 11 V (IPP = 1 A).

#### Industrial Temperature Range

This device features an industrial operating range of  $-40^{\circ}\text{C}$  to  $+125^{\circ}\text{C}$ .



## 14. Typical Application(continued)

Given the USB 2.0 application, the parameters in Table 1 are known.

**Table 1. Design Parameters**

Parameter	Parameter
Signal range on pins 1, 3, 4, or 6	0 V to 5 V
Operating frequency	240 MHz

### Detailed Design Procedure

Signal Range on Pins 1, 3, 4, or 6

The TPD4E1U06 has 4 identical protection channels for signal lines. The symmetry of the device provides flexibility when selecting which of the 4 I/O channels protect which signal lines. Any I/O supports a signal range of 0 to 5.5 V.

### Operating Frequency

The TPD4E1U06 has a capacitance of 0.8 pF (typical), supporting USB 2.0 data rates.

### Application Curve

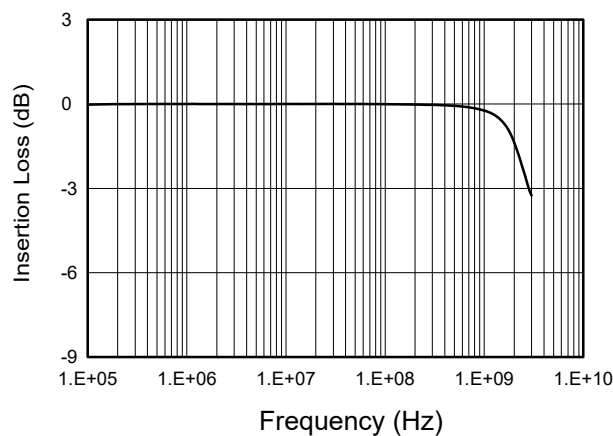
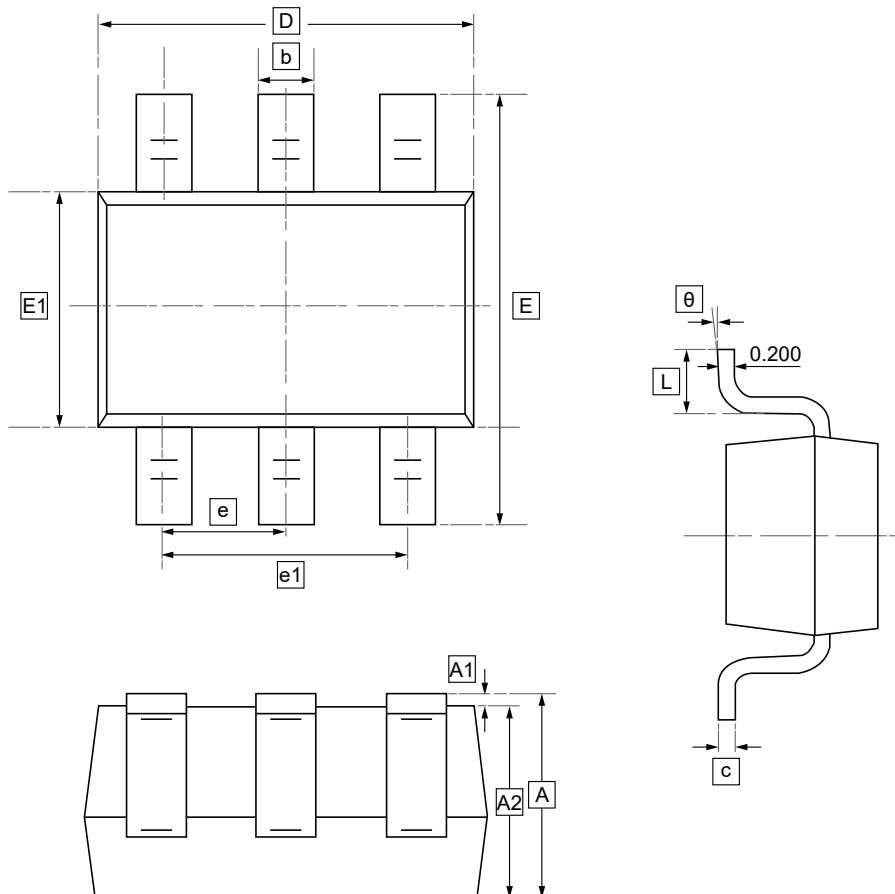


Figure 11: Insertion Loss Graph



## 8.SOT-23-6 Package Outline Dimensions

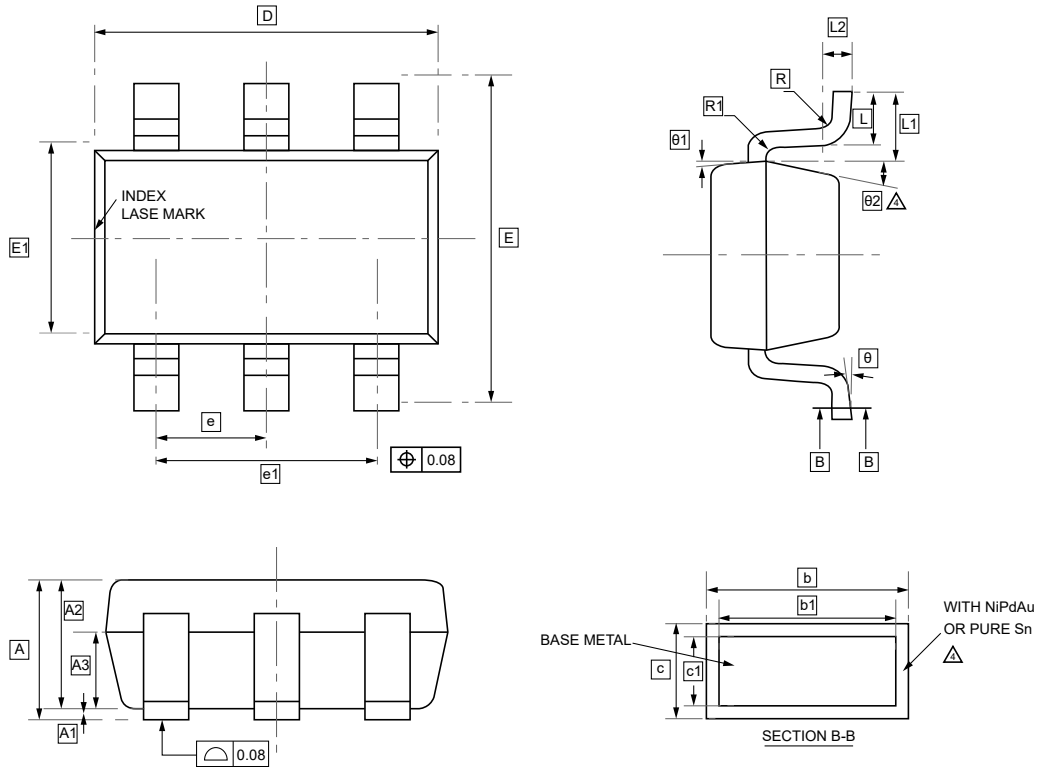


### DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	b	c	D	E1	E	e	e1	L	θ
Min	1.050	0.000	1.050	0.300	0.100	2.820	1.500	2.650	0.950	1.800	0.300	0°
Max	1.250	0.100	1.150	0.500	0.200	3.020	1.700	2.950	BSC	2.000	0.600	8°



16.SC70-6 Package Outline Dimensions



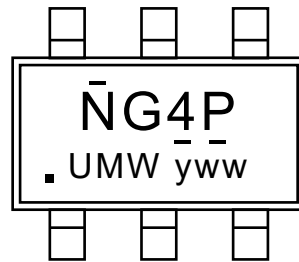
DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	A3	b		b1	c		c1	D	E	E1	e	e1	L
					NiPdAu	PURE Sn		NiPdAu	PURE Sn							
Min	0.85	0	0.80	0.47	0.22	0.23	0.22	0.115	0.12	0.115	2.02	2.20	1.25	0.60	1.20	0.28
Max	1.05	0.10	1.00	0.57	0.29	0.33	0.28	0.15	0.18	0.14	2.12	2.40	1.35	0.70	1.40	0.38

Symbol	L1	L2	R	R1	θ	θ1	θ2
Min	0.50	0.15	0.10	0.10	0°	6°	6°
Max	REF	BSC	-	0.25	8°	12°	12°



## 17. Ordering information



yww: Batch Code

Order Code	Package	Base QTY	Delivery Mode
UMW TPD4E1U06DBVR	SOT23-6	3000	Tape and reel
UMW TPD4E1U06DCKR	SC70-6	3000	Tape and reel



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